

Inventor: Garo J. D rd rian et al.

Title: Methods of F rming Particl -Containing Materials; and S mi-
conductor Constructions Comprising Particle-Containing Materials

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is directed to the references listed on the attached Form PTO-1449. Copies of the cited art are included with the exception of U.S. patents and published U.S. applications (1276 Off. Gaz. Pat. Off., 55, 05 Aug. 2003). No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Date: 12/1/03

Attorney: 

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EL979949505

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2297		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Garo J. Derderian et al.			
				FILING DATE Filed Herewith		GROUP Unknown	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,444,495 B1	09/02	Leung et al.			
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AB			Frank, M. et al., "Enhanced Initial Growth of Atomic-Layer-Deposited Metal Oxides on Hydrogen-Terminated Silicon", App. Phys. Lett., Vol. 83, No. 4, July 28, 2003, pp. 740-742.			
	AC			Rosidian, A. et al., "Formation of Ultrahard Metal Oxide Nanocluster Coatings at Room Temperature by Electrostatic Self-Assembly", SPIE Vol. 3675 (1999), pp. 113-119.			
	AD			Sakaue, H. et al., "Conformable CVD of SiO ₂ into Deep Trench Using the Digital Method", Extended Abstracts of the 22nd (1990 International) Conf. on Solid State Devices and Materials, Sendai (1990), pp. 921-924.			
	AE			Mountziaris, T. et al., "Gas-Phase and Surface Chemistry in Electronic Materials Processing", Materials Research Society Symposium Proceedings, Vol. 334, held 11/29/93 - 12/2/93, Boston, MA, pp. 1-36.			
	AF			Perez, I. et al., "Fabrication and Characterization of 4H-SiC MOS Capacitors with Atomic Layer Deposited (ALD) SiO ₂ ", IEEE 7/00, pp. 144-147.			
	AG			Sakaue, H. et al., "Digital Chemical Vapor Deposition of SiO ₂ Using a Repetitive Reaction of Triethylsilane/Hydrogen and Oxidation", JP Journal of App. Phys., Vol. 70, No. 1B, Jan. 1991, pp. L 124-L 127.			
	AH			Klaus, J. et al., "Atomic Layer Deposition of SiO ₂ at Room Temperature Using NH ₃ -Catalyzed Sequential Surface Reactions", Surface Science 447 (2000), pp. 81-90.			
	AI			Cameron, M. et al., "Atomic Layer Deposition of SiO ₂ and TiO ₂ in Alumina Tubular Membranes: Pore Reduction and Effect of Surface Species on Gas Transport", Langmuir 2000, 16, pp. 7435-7444.			
	AJ			Horiike, Y. et al., "Filling of Si Oxide into a Deep Trench Using Digital CVD Method", App. Surface Science 46, (1990), pp. 168-174.			
	AK			Wise, M. et al., "Diethyldioxysilane as a New Precursor for SiO ₂ Growth on Silicon", Mat. Res. Soc. Symp. Proc. Vol. 334, (©1994 Materials Research Society), pp. 37-43.			
EXAMINER				DATE CONSIDERED			
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	US2003/ 0026989 A1	Pub. 2/6/03	George et al.			07/16/02
	AB	US2002/ 0137260 A1	Pub. 9/26/02	Leung et al.			01/11/01
	AC						
	AD						
	AE						
	AF						
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	AH						
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	AJ						
	AK						
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
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